

TOSHIBA Thyristor Silicon Planar Type

S6A13

Condenser Discharge Control Applications

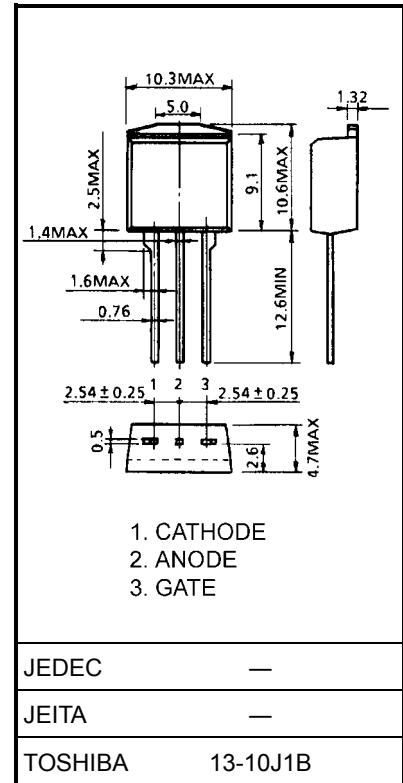
- FWD included between cathode and anode
- Critical rate of rise of ON-state current: $di/dt = 750 \text{ A}/\mu\text{s}$
- Repetitive peak surge ON-state current: $I_{TRM} = 500 \text{ A}$ ($t_w = 2 \mu\text{s}$)
- Repetitive peak OFF-state voltage: $V_{DRM} = 800 \text{ V}$
- Gate trigger current: $I_{GT} = 30 \text{ mA max.}$

Maximum Ratings

| Characteristics | Symbol | Rating | Unit |
|---|------------|---------|------------------------|
| Repetitive peak OFF-state voltage | V_{DRM} | 800 | V |
| Repetitive peak surge ON-state current (Note) | I_{TRM} | 500 | A |
| Repetitive peak surge forward current (Note) | I_{FRM} | 500 | A |
| Critical rate of rise of ON-state current (Note) | di/dt | 750 | $\text{A}/\mu\text{s}$ |
| Peak gate power dissipation | P_{GM} | 5 | W |
| Average gate power dissipation | $P_G (AV)$ | 0.5 | W |
| Peak forward gate voltage | V_{FGM} | 10 | V |
| Peak reverse gate voltage | V_{RGM} | -5 | V |
| Peak forward gate current | I_{GM} | 2 | A |
| Junction temperature | T_j | -40~125 | $^{\circ}\text{C}$ |
| Storage temperature range | T_{stg} | -40~150 | $^{\circ}\text{C}$ |

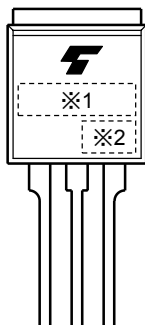
Note: $V_D \leq 0.8 \times \text{rated}$, $T_c = 85^{\circ}\text{C}$, $i_{gp} \geq 60 \text{ mA}$, $t_{gw} \geq 10 \mu\text{s}$, $t_{gr} \leq 150 \text{ ns}$

Unit: mm



Weight: 1.5 g (typ.)

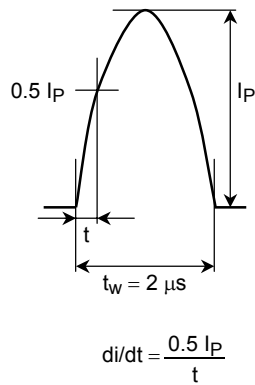
Marking



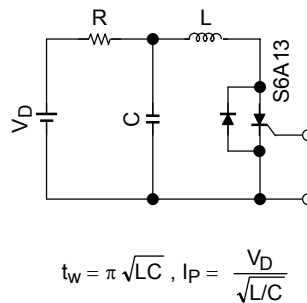
| ※1 | MARK | S6A13 | TYPE NAME | S6A13 |
|----|--|-------|-----------|-------|
| ※2 | Lot Number □ □ ← Month (starting from alphabet A) ↑ Year (last decimal digit of the current year) | | | |

Electrical Characteristics (Ta = 25°C)

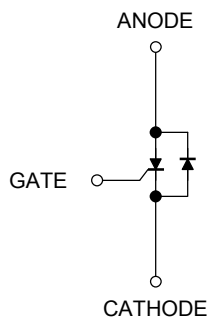
| Characteristics | Symbol | Test Condition | Min | Typ. | Max | Unit |
|--|---------------|---|-----|------|-----|--------------------|
| Repetitive peak OFF-state current | I_{DRM} | $V_{DRM} = \text{Rated}$ | — | — | 10 | μA |
| Peak ON-state voltage (thyristor) | V_{TM} | $I_{TM} = 25 \text{ A}$ | — | — | 1.5 | V |
| Peak forward voltage (diode) | V_{FM} | $I_{FM} = 25 \text{ A}$ | — | — | 2.0 | V |
| Gate trigger voltage | V_{GT} | $V_D = 6 \text{ V}, R_L = 10 \Omega$ | — | — | 1.0 | V |
| Gate trigger current | I_{GT} | | — | — | 30 | mA |
| Gate non-trigger voltage | V_{GD} | $V_D = \text{Rated}, T_c = 125^\circ\text{C}$ | 0.2 | — | — | V |
| Critical rate of rise of OFF-state voltage | dv/dt | $V_{DRM} = \text{Rated}, T_c = 125^\circ\text{C}$ Exponential Rise | — | 50 | — | V/ μs |
| Holding current | I_H | $V_D = 6 \text{ V}, I_{TM} = 1 \text{ A}$ | — | — | 35 | mA |
| Thermal resistance (junction to ambient) | $R_{th(j-a)}$ | DC | — | — | 70 | $^\circ\text{C/W}$ |

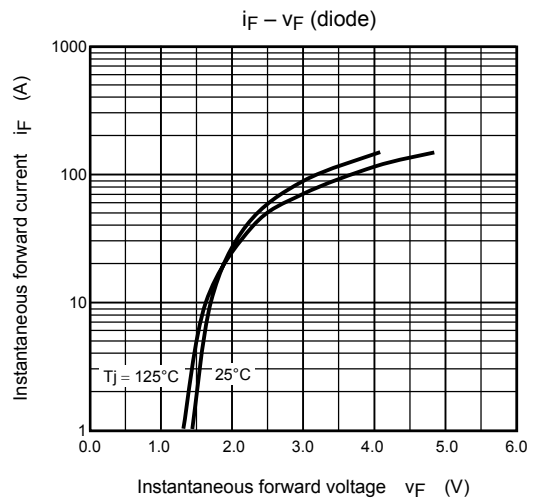
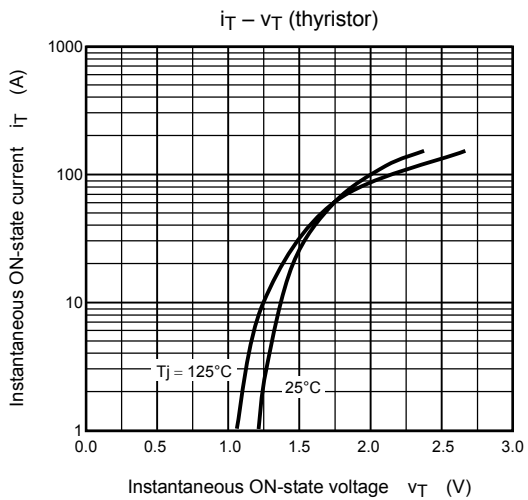
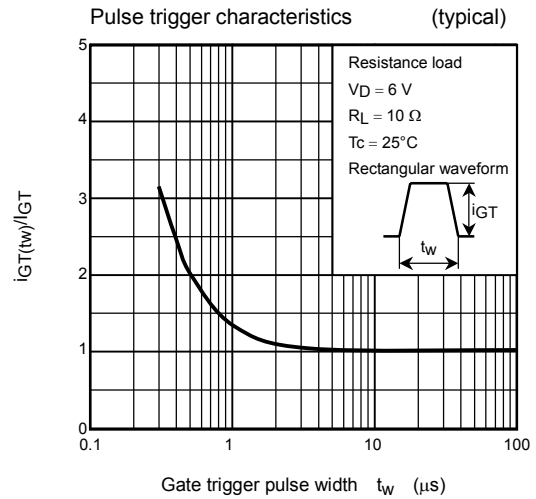
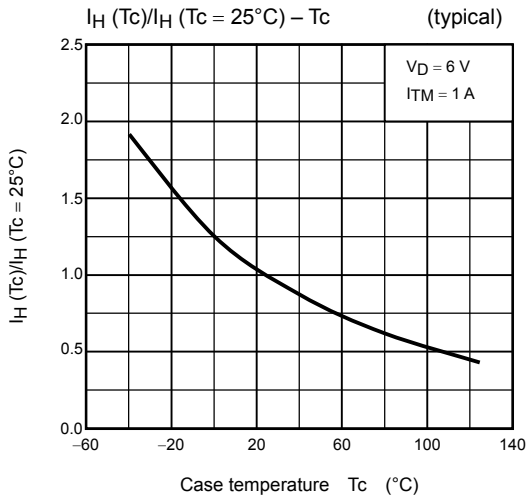
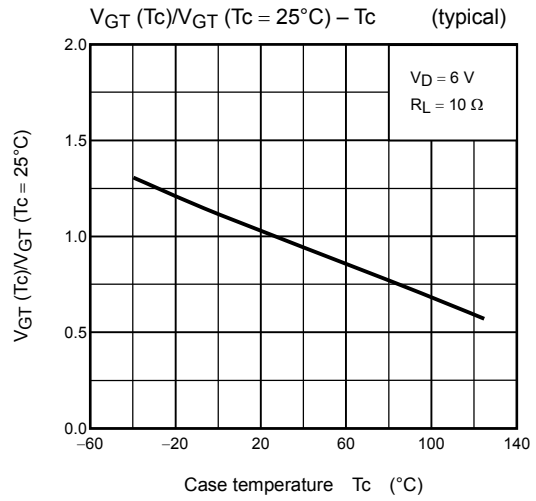
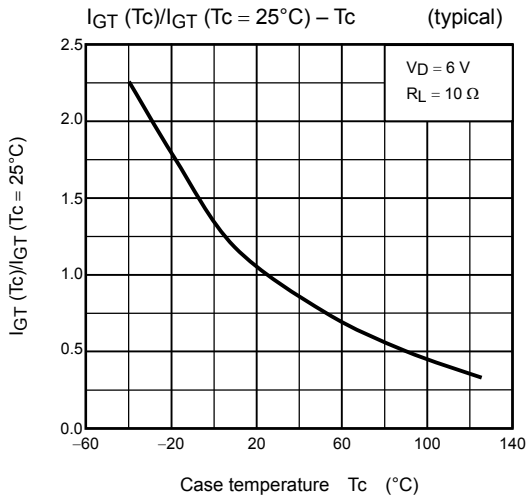


Test Circuit Examples



Equivalent Circuit





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